

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (High Speed U-MOS)

# TPC8005-H

High Speed and High Efficiency DC-DC Converters  
 Lithium Ion Battery Applications  
 Portable Equipment Applications  
 Notebook PC Applications

- Small footprint due to small and thin package
- High speed switching : 60% speed up (compare with current type)
- Small gate charge :  $Q_g = 20 \text{ nC (typ.)}$
- Low drain-source ON resistance :  $R_{DS(ON)} = 13 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance :  $|Y_{fs}| = 16 \text{ S (typ.)}$
- Low leakage current :  $I_{DSS} = 10 \text{ }\mu\text{A (max) (}V_{DS} = 30 \text{ V)}$
- Enhancement-mode :  $V_{th} = 1.3\sim 2.5 \text{ V (}V_{DS} = 10 \text{ V, }I_D = 1 \text{ mA)}$

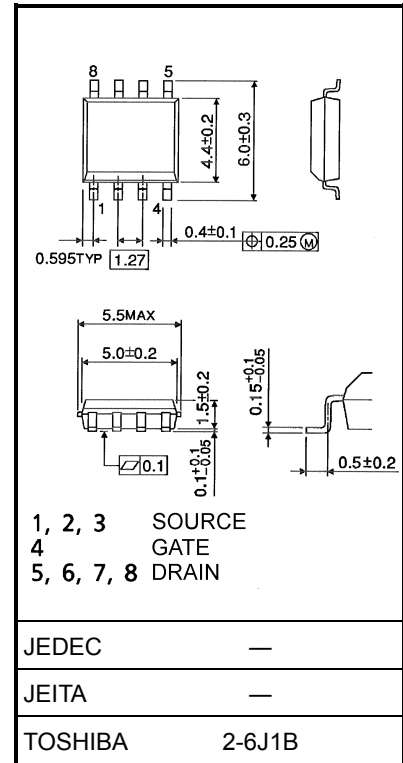
## Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	30	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	11	A
	Pulse (Note 1)	$I_{DP}$	44	
Drain power dissipation (t = 10 s) (Note 2a)		$P_D$	2.4	W
Drain power dissipation (t = 10 s) (Note 2b)		$P_D$	1.0	W
Single pulse avalanche energy (Note 3)		$E_{AS}$	157	mJ
Avalanche current		$I_{AR}$	11	A
Repetitive avalanche energy (Note 2a) (Note 4)		$E_{AR}$	0.24	mJ
Channel temperature		$T_{ch}$	150	°C
Storage temperature range		$T_{stg}$	-55 to 150	°C

Note: For (Note 1), (Note 2), (Note 3) and (Note 4), please refer to the next page.

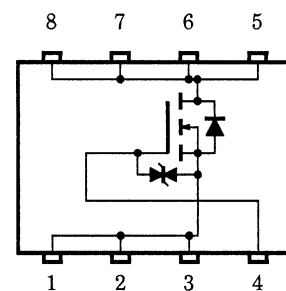
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.080 g (typ.)

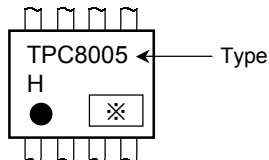
## Circuit Configuration



## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th (ch-a)}$	52.1	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th (ch-a)}$	125	°C/W

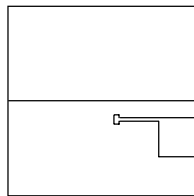
## Marking (Note 5)



Note 1: Please use devices on condition that the channel temperature is below 150°C.

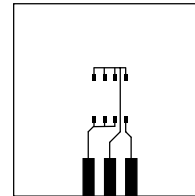
Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)



(a)

FR-4  
25.4 × 25.4 × 0.8  
(unit: mm)



(b)

FR-4  
25.4 × 25.4 × 0.8  
(unit: mm)

Note 3:  $V_{DD} = 24\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 1.0\text{ mH}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = 11\text{ A}$

Note 4: Reptitive rating; pulse width limited by maximum channel temperature

Note 5: ● on lower left of the marking indicates Pin 1.

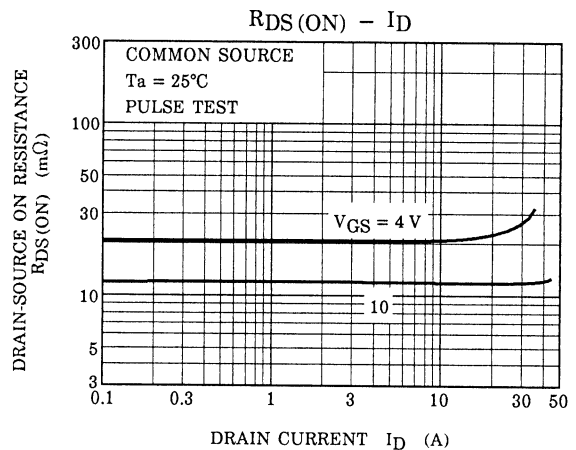
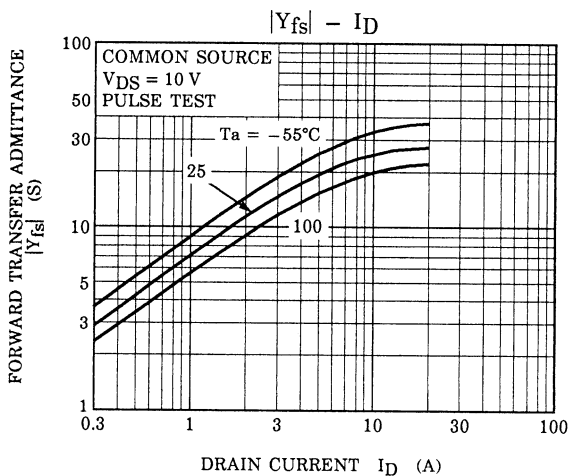
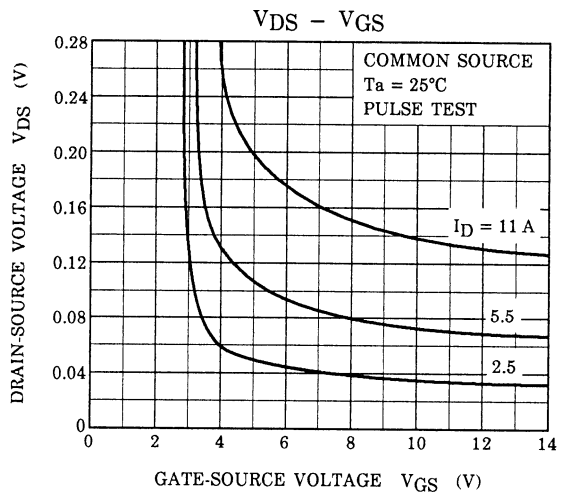
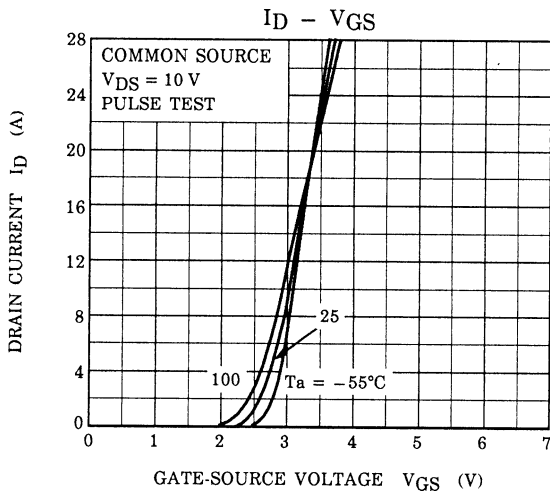
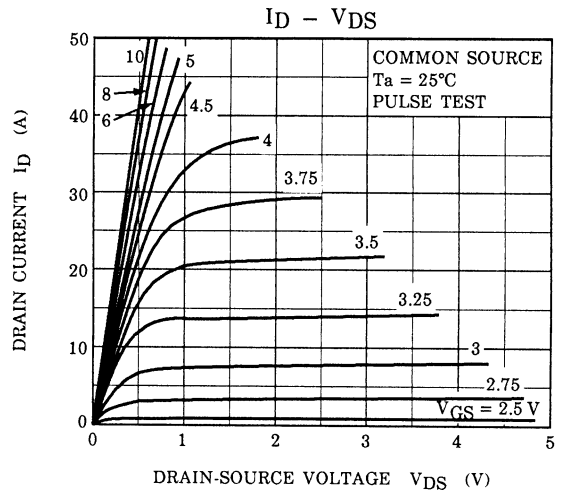
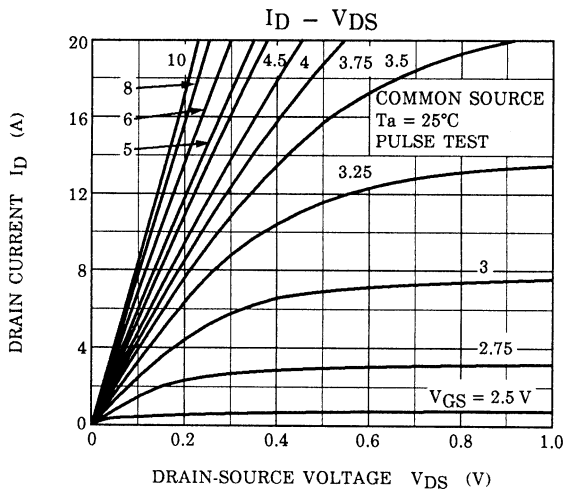
⌘ shows lot number. (year of manufacture: last decimal digit of the year of manufacture, month of manufacture: January to December are denoted by letters A to L respectively.)

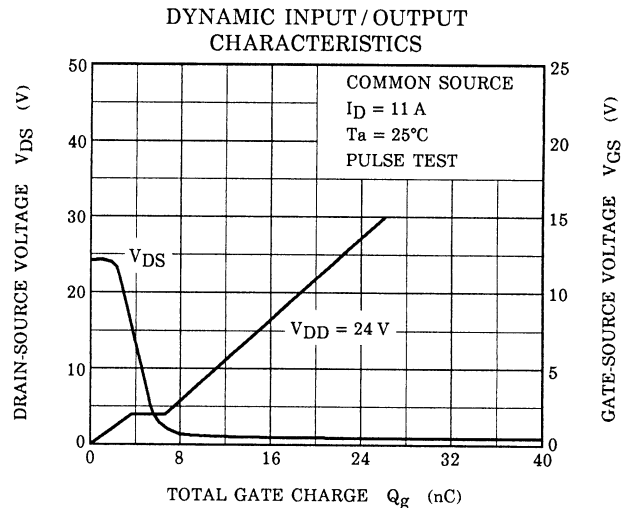
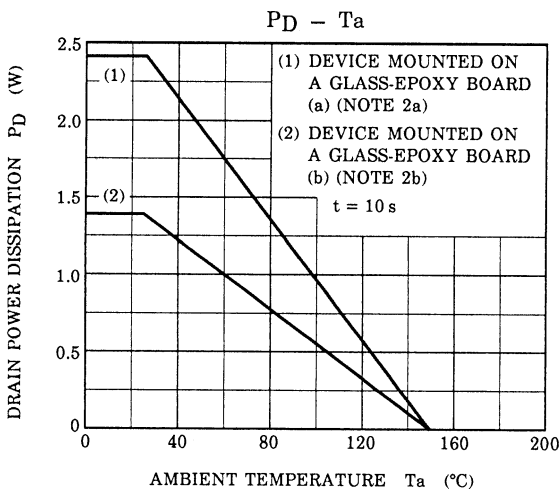
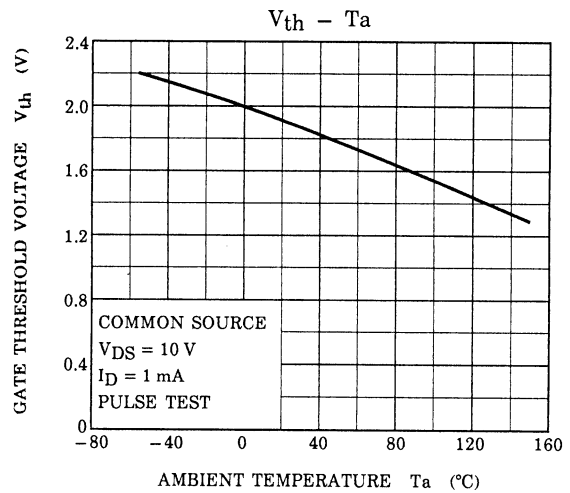
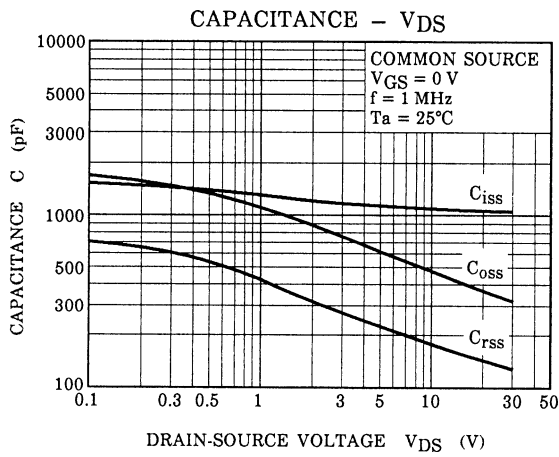
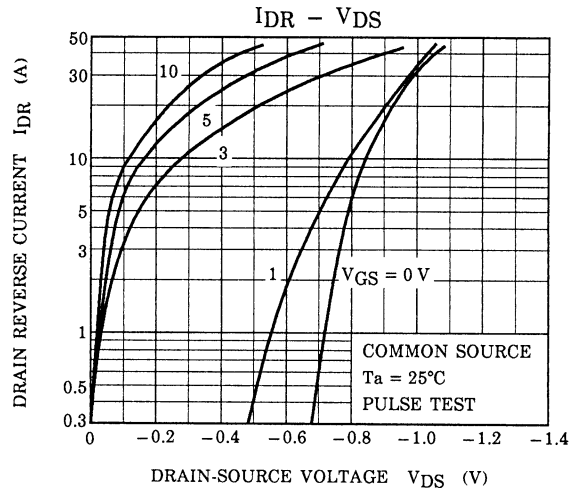
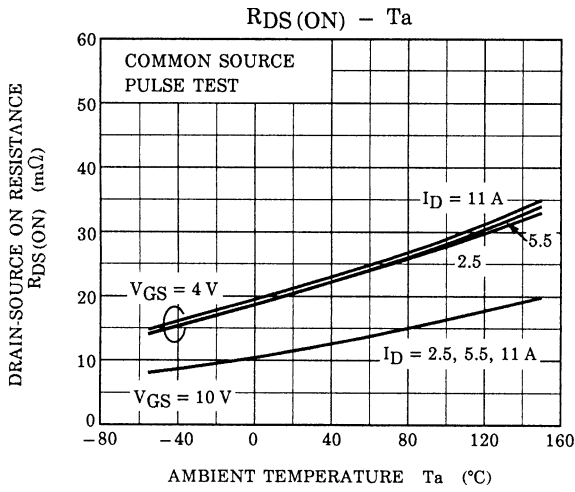
## Electrical Characteristics (Ta = 25°C)

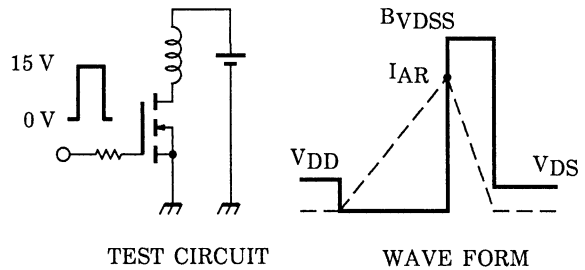
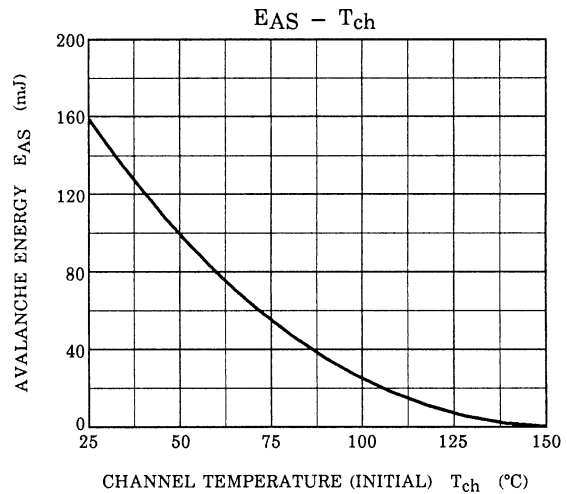
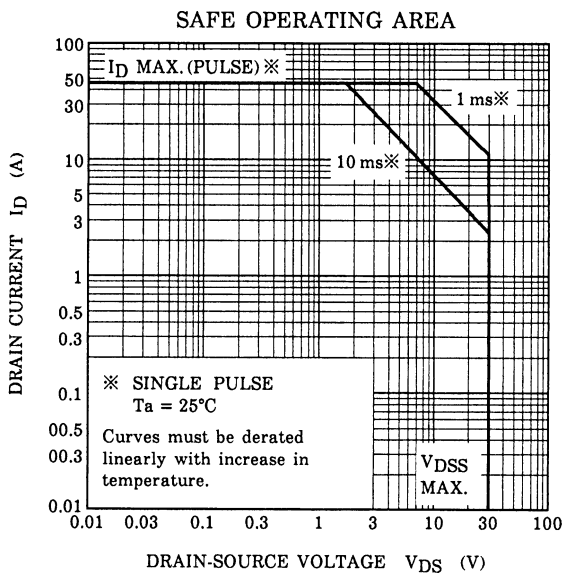
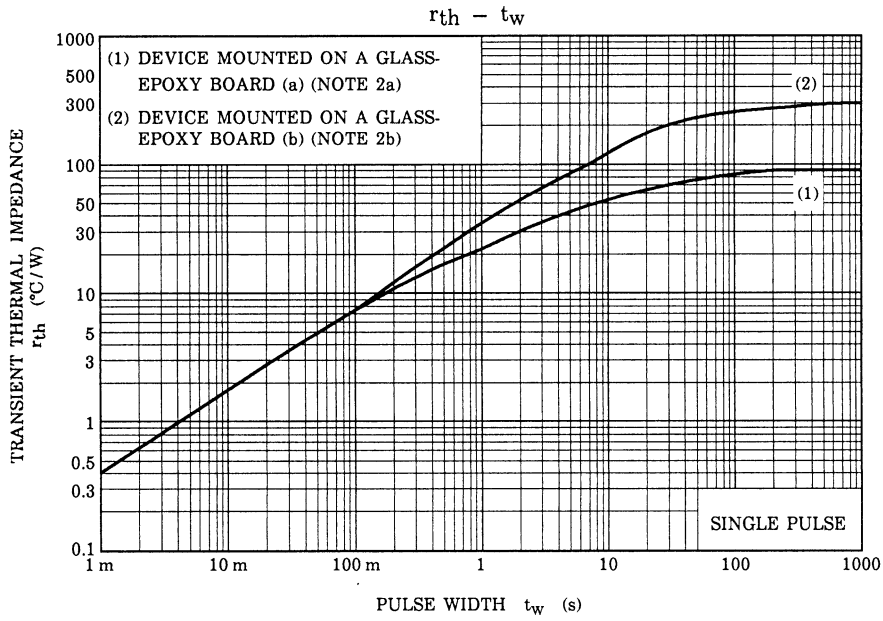
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	10	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	—	—	V
		$V_{(BR)DSX}$	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.3	—	2.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$	—	23	27	$\text{m}\Omega$
		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$	—	13	16	$\text{m}\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 5.5 \text{ A}$	8	16	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1150	—	pF
Reverse transfer capacitance		$C_{rss}$		—	140	—	
Output capacitance		$C_{oss}$		—	400	—	
Switching time	Rise time	$t_r$	<p> <math>I_D = 5.5 \text{ A}</math>  <math>V_{GS} = 10 \text{ V}, 0 \text{ V}</math>  <math>V_{OUT}</math>  <math>R_L = 2.7 \Omega</math>  <math>V_{DD} \approx 15 \text{ V}</math>  <math>\text{Duty} \leq 1\%, t_w = 10 \mu\text{s}</math> </p>	—	4	—	ns
	Turn-on time	$t_{on}$		—	12	—	
	Fall time	$t_f$		—	8	—	
	Turn-off time	$t_{off}$		—	40	—	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}$	—	20	—	nC
Gate-source charge		$Q_{gs}$		—	15	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	5	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	44	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = 11 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.2	V







$T_{ch} = 25^\circ\text{C}$  (Initial)

Peak  $I_{AR} = 11\text{ A}$ ,  $R_G = 25\ \Omega$

$V_{DD} = 24\text{ V}$ ,  $L = 1.0\text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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